
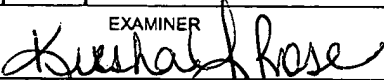


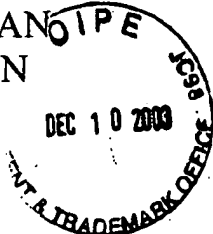
INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 63979-028	SERIAL NO. 10/616,917
				APPLICANT Takashi NISHIKAWA, et al.	
				FILING DATE July 11, 2003	GROUP 2811
U.S. PATENT DOCUMENTS					
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code(s) (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
KR KR		US 2001/0028582 A1	10/11/2001	Tarui et al.	
		US 6,407,435 B1	06/18/2002	Ma et al.	
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FOREIGN PATENT DOCUMENTS					
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code(s)-Number(s)-Kind Code(s) (if known)	Publication Date M of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	<div style="display: flex; justify-content: space-between;"> <div>Translation</div> <div> <div style="text-align: center;">Yes</div> <div style="text-align: center;">No</div> </div> </div>
KR KR	A	JP 08-204404	07/22/1994	HITACHI LTD	Japanese (w/ English Abstract)
		JP 11-168096	06/22/1999	SONY CORP	Japanese (w/Partial English Translation & Abstract)
	A	JP P2002-313968	10/25/2002	NIPPON PRECISION CIRCUITS INC	Japanese (w/ English Abstract)
		EP 1124262	08/16/2001	SHARP KABUSHIKI KAISHA	
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)					
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			
KR		Mitsue Takahashi et al., "ANALYSIS AND IMPROVEMENT OF RETENTION TIME OF MEMORIZED STATE OF METAL-FERROELECTRIC-INSULATOR-SEMICONDUCTOR STRUCTURE FOR FERROELECTRIC GATE FET MEMORY", The Japan Society of Applied Physics, January 5, 2001, pp. 2923-2927			
EXAMINER 		DATE CONSIDERED <div style="font-size: 1.5em;">1/19/05</div>			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

INFORMATION DISCLOSURE CITATION IN AN OPIE APPLICATION

(PTO-1449)


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		US 2001/0028582 A1	10/11/2001	Tarui et al.	
		US 6,407,435 B1	06/18/2002	Ma et al.	
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	A	JP 06-204404	02/22/1994	HITACHI LTD		Japanese (w/ English Abstract)	
		JP 11-168069	06/22/1999	SONY CORP		Japanese (w/Partial English Translation & Abstract)	
	A	JP P2002-313966	10/25/2002	NIPPON PRECISION CIRCUITS INC		Japanese (w/ English Abstract)	
		EP 1124262	08/16/2001	SHARP KABUSHIKI KAISHA			

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		Mitsue Takahashi et al., "ANALYSIS AND IMPROVEMENT OF RETENTION TIME OF MEMORIZED STATE OF METAL-FERROELECTRIC-INSULATOR-SEMICONDUCTOR STRUCTURE FOR FERROELECTRIC GATE FET MEMORY", The Japan Society of Applied Physics, January 5, 2001, pp. 2923-2927

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